

Retraction	Notice

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Correction: yes, date: yyyy-mm-dd X no

#### Comment:

This article has been retracted to straighten the academic record. In making this decision the Editorial Board follows <u>COPE's Retraction Guidelines</u>. Aim is to promote the circulation of scientific research by offering an ideal research publication platform with due consideration of internationally accepted standards on publication ethics. The Editorial Board would like to extend its sincere apologies for any inconvenience this retraction may have caused.



# Heterojunction Photoelectrode of Polyaniline/ZnS Film/ZnO Nanorod on FTO Glass

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## Abstract

To enhance the absorption of visible, the for wide-band-gap semiconductors, methods such as sensinging with nanopal cles or quantum dots, and band gap engineering using dopents have been reported. However, these can cause lattice mismatch, inherent disc ders, or interfect charge balance, which serve as recombination s and significantly duce the photocatalytic efficiency. Here-O on  $F:SnO_2$  (FTO) were fabricated to an-C /7 in, photoelectro PANIA. es . alyze these issued and mine their interface microstructural and photocatananoods (NRs) were grown on FTO glass by lytic ties. electro, eposition, and ZnS and PANI films were coated by liquid pot diostati e PAN films were applied as a visible light sensitizer and DCe photocol sion production layer for ZnS/ZnO photoelectrodes. Subsequently, e prevent in effect of photocurrent loss due to the photocorrosion of semisystematically investigated. The photocurrent of the ductors PANZnS/ZnO photoelectrode measured at 0.5V under white light illumination was five times higher than that of the ZnO NR photoelectrode. This was attributed to photocorrosion prevention and visible light absorption of PANI layers, due to proper energy band alignment of the hybrid heterojunction seminductors.

## **Keywords**

Polyaniline, Visible Light Sensitizer, Photocorrosion, Heterojunction, ZnS Shell/ZnO Core

# **1. Introduction**

The solar energy received by the earth consists of ultraviolet (~5%) and visible light (~43%). Nanostructures are important not only for visible-light absorption in the solar spectrum, but also to obtain a high photocatalytic efficiency for semiconductor photoelectrodes. There has been extensive research on various nanostructured photoelectrodes such as nanowires, nanorods, and nanotubes [1]-[6]. Many multilayered heterojunction nanostructures with great penetration depth have been also reported for the absorption of long wavelengths in the visible light spectrum, as well as the efficient charge separation and transfer of excited electrons and holes [7] [8] [9] [10].

One of the methods to enhance visible-light absorption is to adhere inorganic semiconductors with narrow-band-gap materials such as nanoparticles or quantum dots (QDs) on the surface of wide-band-gap semiconductors, as a sensitizer [11] [12] [13]. Another way is to manipulate the band gap sufficiently to obtain a visible light spectrum response of 1.7 - 2.9 eV by doping impurities such as carbon, nitrogen, or hydrogen [14] [15].

Regarding visible-light sensitizers, studies on chalcogenide compound QDs eV) have been reportsuch as CdS (Eg = 2.4 eV), CdSe (1.7 eV), and Cd<sup>S</sup> ed [16], as well as those on plasmonic Ag and A nanopart, les [17], transition metal dichalcogenide sheets such as  $MoS_2$  at WS<sub>2</sub> , and m tal halide perovskites such as  $CH_3NH_3PbI_3$  and  $CsPbBr_3$ . How ver, his in portant to develop alternative sensitizer materials, ow gnificant Usadvantages of the to PO. he harmful hature abovementioned materials, such Cd, high cost of noble metals, and unstable moisture process.

and gh doping of single or several impurities, the re-In band gap engineering combination probability f excited electrons and holes is very high near doping sites, which include determative cry al defects such as lattice mismatch at the and de-band-gap semiconductors, unstable ininterface between h sensitiz herent disorders [2] and large imbalance among dopants. Hence, even though light is improved by doping, these recombination sites the abso of visi s of photocatalytic current during the separation and se sigr icant can ca cited electrons and holes. sfer of 

Meanwhile, there are few reports on the photocorrosion of sensitizers such as QDs and nanoparticles attached on wide-band-gap semiconductors or those of semiconductors themselves. As alternatives, polymeric materials have recently been proposed as a prevention layer for photocorrosion. However, systematic studies on the photocatalytic performance using these films have not been reported the far.

In this study, conductive organic polyaniline (PANI,  $\Delta E_{LUMO-HOMO} = 2.4 \text{ eV}$ ) was applied for the core/shell composites of ZnS film/ZnO nanorods (NRs) on F:SnO<sub>2</sub> (FTO) substrates. Subsequently, the performance of PANI as a sensitizer as well as a prevention layer to improve the photocatalytic properties, was evaluated.

#### 2. Methods

In this study, to fabricate the hybrid core/shell heterojunction photoelectrodes, after ZnO NRs were grown on FTO substrates by electrodeposition, ZnS films were formed on the surface of ZnO NRs by chemical dipping of ZnO NRs into Na<sub>2</sub>S solution. Finally, the PANI films were coated by chemical dipping techniques. The detail processes are described below.

### 2.1. Preparation of ZnO NRs/FTO Glass Photoelectrode

ZnO NRs were grown on FTO (resistance = 8  $\Omega$ ·m) glass by potentiostatic electrodeposition [21] [22]. The FTO glass was placed in an aqueous solution of 0.5 mM ZnCl<sub>2</sub> and 0.1 M KCl under oxygen bubbling in a three-electrode electrochemical cell, comprising a counter electrode of Pt mesh and reference electrode of Ag/AgCl/sat. KCl. Electrodeposition was carried out at -1.0 V for ~3 h at room temperature.

### 2.2. Particulate ZnS Film Coating on ZnO NRs

A particulate ZnS film was coated on the surface of the ZnO NRs by immersing the ZnO NR electrode in an aqueous  $0.32 \text{ M} \text{ Na}_2\text{S}\cdot9\text{H}_2\text{O}$  solution for ~12 h. Sulfurization by anion-exchange reaction was carried on m a colonized water bath at 60°C. Na<sub>2</sub>S·9H<sub>2</sub>O was used as an S<sup>2-</sup> anion source to form Zn on the surface of the ZnO NRs, according to the following reaction:

$$ZnO_{(s)} + S^{2-}_{(aq)} + H_2O_{(1)} = ZnS_{a} + 2OH_{(a)}$$

The electrode was then washed with deionized water and absolute ethanol several times and dried at  $80^{\circ}$ C for 2 h in a pyen [23] yet.

## 2.3. PANI Sensitizer coating on Particulate ZnS Film/ZnO NRs

The PANI sensitizer was cated by successive ionic layer adsorption and reaction using ammonium Ifate a provincing agent. First, 0.4 M aniline was disc acr solved in 1 M sulful bich served as a cationic precursor in the first beaker. The converse ontained an oxidant solution of 0.2 M ammonium persulwhich served as an anionic precursor. The electrodes fate in M sy uric act re then nerseu the aniline solution for 60 s for the surface polymerizaof PANI the particulate ZnS film/ZnO NR. Subsequently, the electrodes til mersed in the ammonium persulfate solution for 30 s [25] [26]. were .

#### 2.4. Microstructural Characterization

The hicrostructures of the photoelectrodes were characterized by field-emission anning electron microscopy (FE-SEM; JSM-6500 F, JEOL), field-emission transmission electron microscopy (FE-TEM; 200 kV/JEM-2100F HR, JEOL), and X-ray diffraction (XRD, SWXD, Rigaku). Ultraviolet-visible (UV-vis) absorbance spectra of the electrodes were obtained using an ultraviolet-visible-near infrared (UV-VIS-NIR) spectrophotometer (UV 2600, Shimadzu). XPS was performed using a Thermo VG ESCALAB 250 instrument equipped with a microfocused, monochromatic A1 K $\alpha$  X-ray source (1486.6 eV) and magnetic lens. The X-ray spot size was 500 µm (15 kV, 150 W). The spectra were acquired in the constant analyzer energy mode with a pass energy of 150 eV and 40 eV for overview scans and high-resolution scans, respectively.

#### 2.5. Photoelectrochemical Characterization

The photocurrent densities of the photoelectrodes were measured using a potentiostat (AMT VERSASTAT 3, Princeton Applied Research) with a three-electrode cell comprising Pt mesh as the counter electrode and Ag/AgCl/sat. KCl as the reference electrode separated by a proton exchange membrane in aqueous 0.5 M Na<sub>2</sub>SO<sub>4</sub> (pH = 7.15) electrolyte. Using a 1 kW xenon lamp (Newport) with the infrared wavelengths filtered out by water, 1 cm<sup>2</sup> of the working electrode was exposed. The light irradiance, measured using a thermopile detector, was 100 mW/cm<sup>2</sup>.

## 3. Results and Discussion

#### **3.1. Microstructural Characterization**

In this study, photocatalytic properties of ZnS file LnO N. beterojunctions with PANI layers were investigated. For heterojunction rication, after the mposite fa ZnO NRs were grown on FTO substrate by electro lating, InS layers were formed via sulfurization followed by PAN coatin via cat. surface polymerization. The cross-sectional and sur e FE-S (images of ZnO NRs (Figure 1) show that the hexagonal ZnO No, wh diameter ∩f ′ 0 - 500 nm and lengths of 0.5 - 1.5 µm, were grown vertically.



**Figure 1.** FE-SEM images of coated PANI on sulfurized ZnO NRs core. Cross sectional and surface views for ZnO NRs/FTO (a) & (b), particulate ZnS film/ZnO NRs/FTO (c) & (d), and PANI/particulate ZnS film/ZnO NRs/FTO (e) & (f), respectively.

The top surface of the prepared ZnO NRs was dominantly composed of slanted side faces of  $\{10\overline{1}1\}$  crystal planes rather than flat hexagonal  $\{0001\}$  crystal planes. Compared to the hexagonal  $\{0001\}$  planes,  $\{10\overline{1}1\}$  crystal planes have lower stacking density, and thus, higher surface energy. The hydrothermal growth

rate of ZnO NRs on FTO is determined primarily by the diffusion rate of Zn<sup>2+</sup> ions during the process, and ion diffusion into side {10ī1} planes is much more than that into top {0001} surfaces, such that the hydrothermally grown ZnO NRs show wide {0001} crystal planes on their top surfaces. On the other hand, electroplated ZnO NRs have narrow and sharp top surfaces composed of hexagonal {0001} planes, because Zn<sup>2+</sup> concentration is much higher in the top surfaces due to higher electroplating potential. However, many voids are observed on the surface of ZnO NRs (**Figure 1**), probably formed by O<sub>2</sub> gas bubbles in the electroplating bath, which disturbed the migration of Zn<sup>2+</sup> ions on the surface.

Meanwhile, for fabrication of heterojunction composites with efficient charge separation, the ZnS films were coated on the surface of ZnO NRs via ion exchange sulfurization. When the ZnO NRs were dipped in the provident solution, the O<sup>2-</sup> ions on the ZnO surface and the  $S^{2-}$  ions in the Na<sub>2</sub>S solution were exchanged to form ZnS particles on the surface of ZnO NRs. The cross-station and urface images of ZnS films/ZnO NRs fabricated by the cesses are shown in Figure 1(c) and Figure 1(d). As shown in Figure 1(d) the 2 S ins consist of stacked agglomerates of ~25 nm nanoparticles. The pross-section and surface images of the 5 film/ZnO NRs are shown conductive organic sensitizer, FANI, conted on the espective. As shown in Figure 1(f), the smooth in Figure 1(e) and Figure urrounded by both 2nS film composed of stacked agsurface of a ZnO NR is d PANI fil glomerated nanoparticles a

TEM images one NI/ZnSchm/ZnONRs (Figure 2(a) and Figure 2(b)) show that a core electroc poster. ZnO NR is surrounded by both ~5-nm-thick PANI film and so one-thick particulate ZnS film. Thus, this core/shell structure should preven direct ontact of ZnO NRs with the electrolyte in the photocatalytic cells, this preventing detribution of photocatalytic current due to photocorrosion.

ANS films a ZnO NRs can be typically formed by several methods like chemical a porption or ZnS nanoparticles and vapor-liquid-solid (VLS) methods.



**Figure 2.** TEM (a) bright field and (b) lattice fringe images of the PANI/particulate ZnS film/ZnO NRs, and (c) selective area electron diffraction pattern of the interface between particulate ZnS film and ZnO NRs, respectively.

However, for direct adhesion of ZnS nanoparticles on the ZnO surface, micro-voids can occur in the sites between the ZnS nanoparticles. The lattice mismatch between the ZnS nanoparticles and ZnO NRs can also cause the interface defects. Thus, annealing processes are necessary for reduction of these crystalline defects.

In the VLS methods using Zn and S powder sources, non-uniform adsorption of

Zn and S vapors on the surfaces of ZnO NRs, which have different surface states depending on crystal orientations, results in anisotropic growth of ZnS. Thus, it is difficult to obtain dense ZnS films using this technique, but thick films can be obtained. However, in the surface sulfurization processes, uniform ZnS films can be feasibly formed, because ZnS nanoparticles are formed by ion exchange of  $O^{2^-}$  ions on the ZnO surface and  $S^{2^-}$  ions in the solution. Furthermore, the crystal orientations of ZnO NRs have negligible effect on the growth of ZnS because the ZnO surface is surrounded by water molecules in the solution.

The PANI film synthesized by polymerization was deposited relatively uniformly on the ZnS film. Selected area electron diffraction patterns for the interface between particulate ZnS film and ZnO NRs are shown in **Figure 2(c)**. Polycrystalline ring patterns and single-crystalline dot patterns were observed for the particulate ZnS film and the ZnO NR, respectively. Electron diffraction patterns from (100), (101), and (102) ZnO (zincite space group 263mc; JCPDS card no. 36-1451) for the [0ī0] zone axis were observed, confirming the nexagonal Wurtzite structure of ZnO NRs.

However, the electron diffraction petterns of the Zpe Alm corresponded to both the (111) sphalerite cubic phase (space group F43m; JCPDS card no. 05-0566) and the hexagonal (008) he agonal phase (space group P63mc; JCPDS card no. 39-1363), which have interplanar distances of 3.123 Å and 3.120 Å, respectively. At this point, therefore the ZnS is no clear. However, other groups using similar ZnS synthesis processes report a cubic zinc blende (111) peaks at  $2\theta = 28.62^{\circ}$  in XRD metans.

The XRD patterns for PANI/particulate ZnS film/ZnO NRs/FTO samples (**Figure 3**, inclusion that the peaks  $(2\theta = 31.8^{\circ}, 34.5^{\circ}, 36.3^{\circ}, 47.6^{\circ}, 56.5^{\circ}, \text{ and } 62.9^{\circ})$  of **X** O NRs correspond to the (100), (002), (101), (102), (110), and (103) crystal plane, respectively, of the hexagonal crystal lattice of zincite (space group P63mc; NPDS card no. 36-1451). The peak at  $2\theta = 28.61^{\circ}$  corresponds to the cubic ZnS (111) crystal plane. However, the XRD peaks of PANI layer were not observed. This resulted from the amorphous phase of the PANI layer after the synthesis and dip-coating, whereas other group has reported for the polycrystalline PANI synthesis. This discrepancy was attributed to different processes including sources for the PANI synthesis [27].

The PANI layer and compositional surface analysis of the ZnS film/ZnO NRs were characterized by using X-ray photoelectron spectroscopy (XPS), and the analysis results are shown in **Figure 4**. Zn  $2p_{1/2}$  (1,045 eV), Zn  $2p_{3/2}$  (1,020 eV) and O 1s (531 eV) peaks were observed for ZnO NRs, and S 2s (226 eV) and S 2p



Figure 4. XPS spectra of (a) PANI/particulate ZnS film/ZnO NRs, particulate ZnS film/ZnO NRs and ZnO NRs, respectively, and (b) chemical element N 1s peak composed of imine s  $R^3-N = C-R^1R^2$  (398.5eV), amine as  $R^1R^2-NH$  (399.7 eV) and protonated nitrogen as A = (401.9eV).

(162 eV) peaks were observed for ZnS films. On the other hand, N 1s (399 eV) at C 1s (285 eV) peaks were observed for PANI. The N 1s (399 eV) peak, consisting of imine  $R^3-N = C-R^1R^2$  (398.5 eV), amine  $R^1R^2-NH$  (399.7 eV), and protonated nitrogen  $-N^+ = (401.9 \text{ eV})$  signals, originated from the N element of the aniline monomer, as shown in **Figure 4(b)** [28].

### **3.2. Photoelectrochemical Characterization**

The UV-Vis absorption spectra of PANI/ZnS film/ZnO NRs, ZnS film/ZnO NRs, and ZnO NR electrodes were measured as shown in **Figure 5(a)**. All the spectra present a strong absorption in the UV region between 300 and 400 nm. The band gaps of each layers were estimated from the Tauc plots [29] as shown in **Figure 5(b)**. The values from the line intersections were measured as 3.12, 3.16, and 2.7 eV for ZnO NRs, ZnS film/ZnO NRs, and PANI/ZnS film/ZnO



**Figure 5.** (a) UV-Vis absorption spectra and (b) the plot for band gap calculation of ZnO NRs, ZnS film/ZnO NRs, and PANI/ZnS film/ZnO NRs electrode, respectively.

ZnO N. NRs, respectively d with the ZnS film of the wide band gap The showed slightly incr sed a gap, that is blue-shifting absorption. However, the weak absorp on in the visible region between 400 and 500 nm was obwide a ed ZnS film/ZnO NRs sample. This resulted in the reser d the ANI co. ced band, up of 2.7 in the Tauc plot. Thus this is due to the narrow band gap PANI lay in the range from  $\sim 2.4 \text{ eV}$  to  $\sim 2.8 \text{ eV}$  [30]. of

Photourrent densities of the samples were measured in a photoelectrochemical (PEC) cell order exposure of white light consisting of UV and visible light (see **Figure 6(a)** ZnO, **Figure 6(b)** ZnS/ZnO, and **Figure 6(c)** PANI/ZnS/ZnO, respective ). Photocurrent density corresponding to the pure photoresponse by using a hopping light source (on-off) was measured. The measured photocurrent density was the photoresponse difference between the on- and off-states of the light source.

Under white light illumination, the representative photocurrent densities of ZnO NRs, ZnS film/ZnO NRs, and PANI/ZnS film/ZnO NRs were 0.173 mA/cm<sup>2</sup>, 0.461 mA/cm<sup>2</sup>, and 0.865 mA/cm<sup>2</sup>, respectively, at 0.5 V. The PANI/ZnS film/ZnO NR electrode showed about 5- and 1.8-times larger photocurrent density than the ZnO NRs and ZnS film/ZnO NRs, respectively. The ZnS film/ZnO NR electrode showed about 2.7-times larger photocurrent density than the ZnO NRs.

These measurement results confirm the light absorption spectral analysis results (**Figure 5**). The photocurrent densities of PANI/ZnS film/ZnO NRs were significantly improved due to superior visible light absorption properties of the



Figure 6. Photocurrent density of (a) ZnO NRs, (b) ZnS film/ZnO NRs, and (c) PANI/ZnS film/ZnO NRs electrodes under white light (UV and visible light) irradiation.

PANI layers. The PANI band gap was 2.7 eV as shown in **Figure 5(b)**. Furthermore, both PANI/ZnS film/ZnO NRs and ZnS film/ZnO terojunction have good enough combination of potential levels (energy base alignment) to transfer and efficiently separate excited electrons and holes [12] [32, [33] [34].

In summary, PANI/ZnS film/ZnO N/ photoelectro fabricated and evaluated for their photocatalytic per ine hexagonal ZnO ma e. Igle-cryst. own on **F** glass NRs of lengths 0.5 - 1.5 µm were bic ZnS films consisting of 5 - 10-nm nanoparticles vere co ted with the less of ~30 nm on the ZnO with thick, ss of ~5 nm were coated on the ZnS NRs and organic PANI films. XRD and XPS analyses showed strong eaks for ZnS (111) and ZnO (002) polecular bonding structure were observed crystal planes, and C/N et nents and for PANI.

#### 4. Conclusion

NI/ZnS ZnO/FTO electrodes were studied on their interface and In this udy, J . Unu. hite light illumination, the PANI/ZnS film/ZnO NR elecotocata tro showed times higher photocurrent density than ZnO NRs. This was due to the nti-photocorrosion and visible light absorption of PANI layer, and also oper energy band alignment of the hybrid heterojunction (PANI/ZnS provided film/ZnO NRs) to efficiently transfer and separate excited electrons and holes. It is ed that this hybrid heterojunction photoelectrode with proper band alignnt using organic materials could be utilized for other applications such as photovoltaics, solar CO<sub>2</sub> fuel conversion, and solar pollutant decomposition.

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#### **Conflicts of Interest**

The authors declare no conflicts of interest regarding the publication of this paper.

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